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TECHNOLOGY CENTER 2800

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February 28, 2003

VIA FACSIMILE

To: Examiner Ahmed N. Sefer
Group Art Unit No. 2826
U.S.P.T.O.

Facsimile No.: (703) 872-9319

From: Phillip E. Miller

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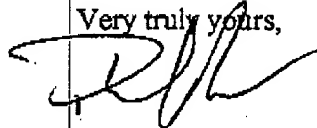
Re: Enclosed § 1.116 Amendment
U.S. Patent Application Serial No. 09/985,927
Our Ref: NGB.177

Dear Examiner Sefer:

Enclosed is the Amendment, responsive to the December 19, 2002 Final Office Action, which should place the above-referenced case in condition for allowance.

Thank you in advance for your consideration on this case.

Very truly yours,



Phillip E. Miller

PEM/cc

Enclosure

Total No. of Pages Transmitted: 9

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of

Naoki SHIBATA et al.

Serial No.: 09/985,927

Filed: November 6, 2001

For: GROUP III NITRIDE COMPOUND SEMICONDUCTOR DEVICE AND METHOD
FOR PRODUCING THE SAME

Honorable Commissioner of Patents
Washington, D.C. 20231
Box AF

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Group Art Unit: 2826

TECHNOLOGY CENTER 2000

Examiner: Ahmed N. Sefer

AMENDMENT UNDER 37 C.F.R. §1.116

Sir:

In response to the Office Action dated December 19, 2002, please amend the above-identified application as follows:

IN THE CLAIMS:

Please amend the claims to read as follows:

5. (Twice Amended) A group III nitride compound semiconductor device comprising:
a substrate on which a first environment division and a second environment division are formed; and
group III nitride compound semiconductor layers formed on said first environment division so as to serve as effective semiconductor layers,
wherein said first environment division comprises an outer shape having rounded corners.